

μA9645(3245) Quad TTL To MOS/CCD Driver

Linear Division Interface Products

Description

μA9645(3245) is a high speed driver intended to be used as a clock (high level) driver for 18 or 22-lead dynamic NMOS RAMs. It also satisfies the non-overlapping phase clock drive requirements for CCD memories like F464 (64K) RAM.

The circuit is designed to operate on nominal +5.0 V and +12 V power supplies and contains input and output Schottky diodes to minimize line reflections.

The device features two common enable inputs, a refresh control input and a clock control input. Internal gating logic is organized so that all four drivers may be deactivated for standby operation, or a single driver may be activated for read/write operation or all four drivers may be activated for refresh operation.

μA9645(3245) is a lead for lead replacement of the μA3245 Quad TTL-to-MOS Driver, with substantially reduced DC power dissipation.

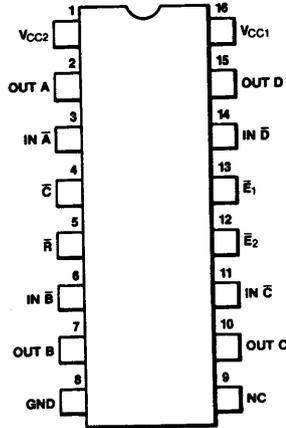
- Interchangeable With Intel 3245
- Four High Speed, High Current Drivers
- Control Logic Optimized For MOS RAMs
- Satisfies CCD Memory And Delay Line Drive Requirements
- TTL And DTL Compatible Inputs
- High Voltage Schottky Technology

Absolute Maximum Ratings

Storage Temperature Range	-65°C to +175°C
Ceramic DIP	-65°C to +150°C
Molded DIP	0°C to +70°C
Operating Temperature Range	
Ceramic DIP	300°C
Molded DIP (soldering, 60 s)	265°C
Molded DIP (soldering, 10 s)	
Normal Power Dissipation ^{1,2}	
16L-Ceramic DIP	1.50 W
16L-Molded DIP	1.04 W
Supply Voltage, V _{CC1}	-0.5 V to +7.0 V
Supply Voltage, V _{CC2}	-0.5 V to +14.0 V
Input Voltages	-1.0 V to V-
Inputs For Clock Driver	-1.0 V to (V-) +1.0 V
Temperature Under Bias	-10°C to +70°C

¹ T_J Max = 175°C for the Ceramic DIP, and 150°C for the Molded DIP.
² Ratings apply to ambient temperature at 25°C. Above this temperature, derate the 16L-Ceramic DIP at 10 mW/°C, and the 16L-Molded DIP at 8.3 mW/°C.

**Connection Diagram
16-Lead DIP
(Top View)**



CD00311F

Order Information

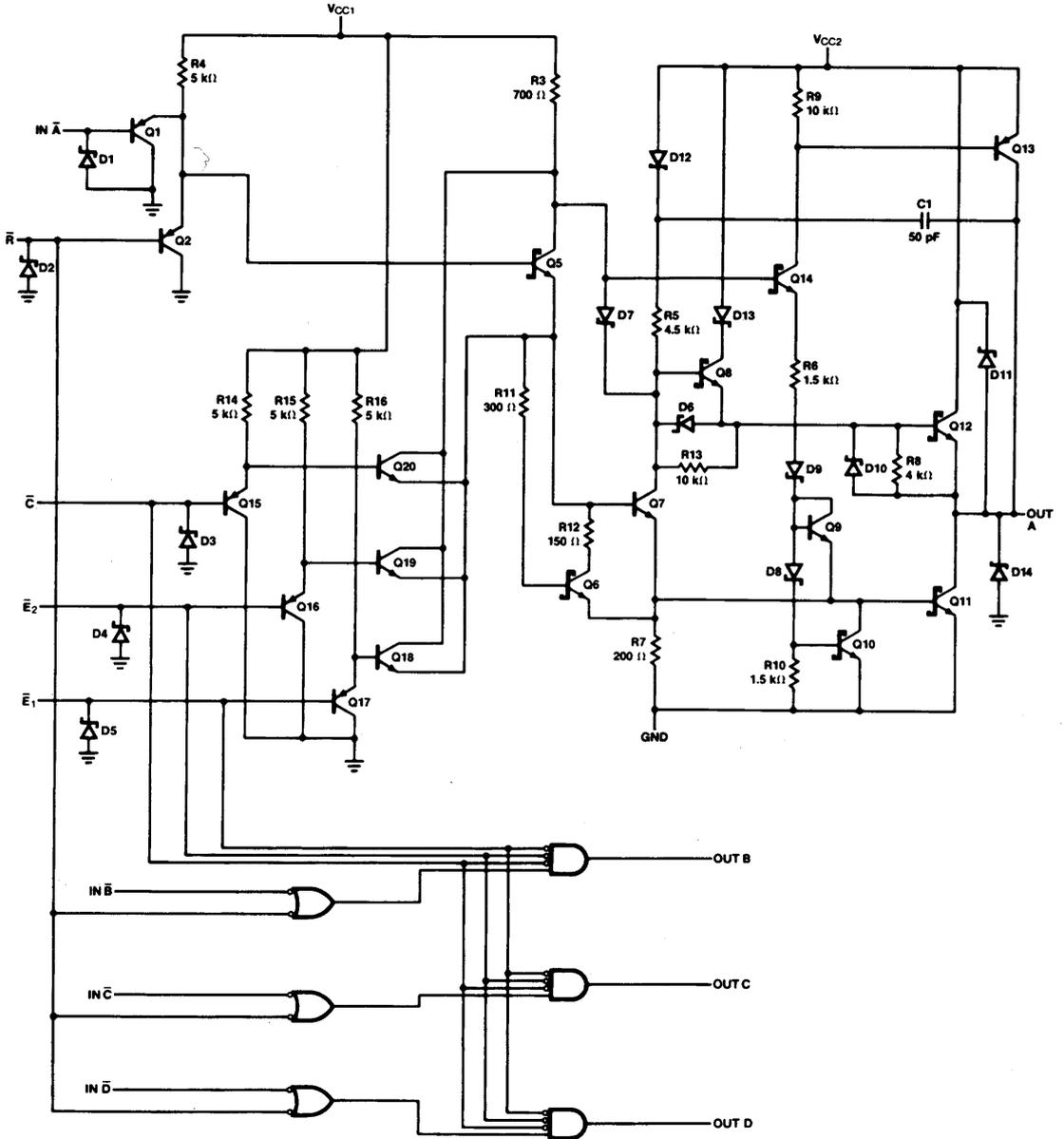
Device Code	Package Code	Package Description
μA9645DC(3245)	7B	Ceramic DIP
μA9645PC(3245)	9B	Molded DIP

Truth Table

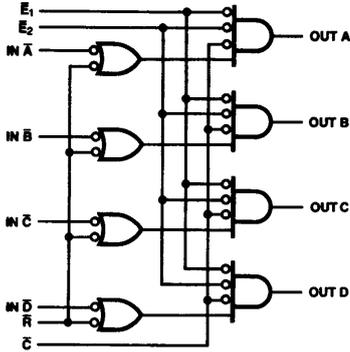
Inputs					Output
Control			Address		
C	E ₂	E ₁	INPUT	REFRESH	
H	X	X	X	X	L
X	H	X	X	X	L
X	X	H	X	X	L
X	X	X	H	H	L
L	L	L	L	X	H
L	L	L	X	L	H

H = HIGH
 L = LOW
 X = Don't Care

Equivalent Circuit



Logic Diagram



CD00020F

Electrical Characteristics

$V_{CC1} = 5.0 \text{ V} \pm 5\%$, $V_{CC2} = 12 \text{ V} \pm 5\%$, $T_A = 0^\circ\text{C}$ to 70°C , unless otherwise specified.

Characteristics

Symbol	Characteristic	Condition	Min	Typ	Max	Unit
I_{IN}	Input Load Current, IN ($\bar{A}, \bar{B}, \bar{C}, \bar{D}$)	$V_F = 0.45 \text{ V}$			-0.25	mA
$I_{E1, E2}$	Input Load Current, $\bar{R}, \bar{C}, \bar{E}_1, \bar{E}_2$	$V_F = 0.45 \text{ V}$			-1.0	mA
I_{IN}	Data Input Leakage Current	$V_R = 5.0 \text{ V}$			10	μA
$I_{E1, E2}$	Enable Input Leakage Current	$V_R = 5.0 \text{ V}$			40	μA
V_{OL}	Output Voltage LOW	$I_{OL} = 5.0 \text{ mA}, V_{IH} = 2.0 \text{ V}$ $I_{OL} = -5.0 \text{ mA}$			0.45	V
V_{OH}	Output Voltage HIGH	$I_{OH} = -1.0 \text{ mA}, V_{IL} = 0.8 \text{ V}$ $I_{OH} = 5.0 \text{ mA}$	$V_{CC2} - 0.50$		$V_{CC2} + 1.0$	V
V_{IL}	Input Voltage LOW, All Inputs				0.8	V
V_{IH}	Input Voltage HIGH, All Inputs		2.0			V
I_{CC1H}	Positive Supply Current HIGH	$V_{CC1} = 5.25 \text{ V}$		13	20	mA
I_{CC1L}	Negative Supply Current HIGH	$V_{CC2} = 12.6 \text{ V}$		14	20	mA
P_{CH}	Power Consumption HIGH	All Outputs HIGH		248	357	mW
	Power Per Channel			62	90	mW
I_{CC1L}	Positive Supply Current LOW	$V_{CC1} = 5.25 \text{ V}$		27	35	mA
I_{CC1L}	Negative Supply Current LOW	$V_{CC2} = 12.6 \text{ V}$		12	15	mA
P_{CL}	Power Consumption LOW	All Outputs LOW		296	373	mW
	Power Per Channel			74	94	mW

μA9645(3245)

μA9645(3245) (Cont.)

Electrical Characteristics $V_{CC1} = 5.0 \text{ V} \pm 5\%$, $V_{CC2} = 12 \text{ V} \pm 5\%$, $T_A = 0^\circ\text{C}$ to 70°C , unless otherwise specified.

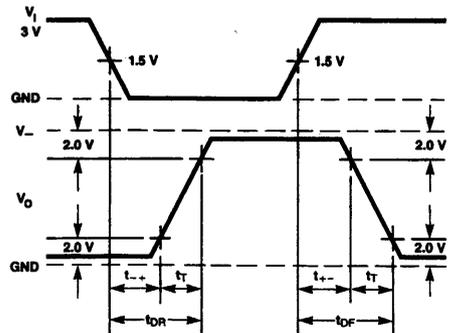
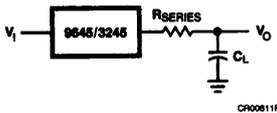
AC Characteristics

Symbol	Characteristic	Condition	Min ¹	Typ ^{2,4}	Max ³	Unit
$t_{- (+)}$	Input to Output Delay	$R_{\text{SERIES}} = 0$	5.0	11		ns
t_{DR1}	Delay Plus Rise Time	$R_{\text{SERIES}} = 0$		18	32	ns
$t_{+ (-)}$	Input to Output Delay	$R_{\text{SERIES}} = 0$	3.0	7.0		ns
t_{DF1}	Delay Plus Fall Time	$R_{\text{SERIES}} = 0$		18	32	ns
t_{T}	Output Transition Time	$R_{\text{SERIES}} = 20 \ \Omega$	10	13	20	ns
t_{DR2}	Delay Plus Rise Time	$R_{\text{SERIES}} = 20 \ \Omega$		27	38	ns
t_{DF2}	Delay Plus Fall Time	$R_{\text{SERIES}} = 20 \ \Omega$		24	38	ns

Notes

1. $C_L = 150 \text{ pF}$
2. $C_L = 200 \text{ pF}$
3. $C_L = 250 \text{ pF}$
4. Typical values are measured at $T_A = 25^\circ\text{C}$

AC Test Circuit and Waveforms



Note

AC Test Conditions:
 Input Pulse Amplitude = 3.0 V
 Input Pulse Rise and Fall Times = 5.0 ns Between 1.0 V and 2.0 V